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EZ-BLE™ PRoC™ Module

General Description

The Cypress CYBLE-022001-00 is a fully certified and qualified module supporting Bluetooth[®] Low Energy (BLE) wireless communication. The CYBLE-022001-00 is a turnkey solution and includes onboard crystal oscillators, chip antenna, passive components, and Cypress PRoC™ BLE. Refer to the CYBL10X6X datasheet for additional details on the capabilities of the PRoC BLE device used on this module.

The CYBLE-022001-00 supports a number of peripheral functions (ADC, timers, counters, PWM) and serial communication protocols (I 2 C, UART, SPI) through its programmable architecture. The CYBLE-022001-00 includes a royalty-free BLE stack compatible with Bluetooth 4.1 and provides up to 16 GPIOs in a small 10 \times 10 \times 1.80 mm package.

The CYBLE-022001-00 is a complete solution and an ideal fit for applications requiring BLE wireless connectivity.

Module Description

- Module size: 10.0 mm ×10.0 mm × 1.80 mm (with shield)
- Bluetooth 4.1 single-mode module
- Industrial temperature range: -40 °C to +85 °C
- 32-bit processor (0.9 DMIPS/MHz) with single-cycle 32-bit multiply, operating at up to 48 MHz
- 128-KB flash memory, 16-KB SRAM memory
- Watchdog timer with dedicated internal low-speed oscillator (ILO)
- Two-pin SWD for programming
- Up to 16 GPIOs configurable as open drain high/low, pull-up/pull-down, HI-Z analog, HI-Z digital, or strong output
- Certified to FCC, CE MIC, KC, and IC regulations
 - ☐ FCC ID: WAP2001 ☐ IC ID: 7922A-2001 ☐ MIC ID: 005-101007

☐ KC ID: MSIP-CRM-Cyp-2001

- Bluetooth SIG 4.1 qualified
 - □ QDID: 67366

□ Declaration ID: D026297

Power Consumption

- TX output power: -18 dbm to +3 dbm
- Received signal strength indicator (RSSI) with 1-dB resolution
- TX current consumption of 15.6 mA (radio only, 0 dbm)
- RX current consumption of 16.4 mA (radio only)

- Low-power mode support
 - Deep Sleep: 1.3 μA with watch crystal oscillator (WCO) on
 - □ Hibernate: 150 nA with SRAM retention
 - □ Stop: 60 nA with XRES wakeup

Functional Capabilities

- Up to 15 capacitive sensors for buttons or sliders with best-in-class signal-to-noise ratio (SNR) and liquid tolerance
- 12-bit, 1-Msps SAR ADC with internal reference, sample-and-hold (S/H), and channel sequencer
- Two serial communication blocks (SCBs) supporting I²C (master/slave), SPI (master/slave), or UART
- Four dedicated 16-bit timer, counter, or PWM blocks (TCPWMs)
- Programmable low voltage detect (LVD) from 1.8 V to 4.5 V
- I²S master interface
- Bluetooth Low Energy protocol stack supporting generic access profile (GAP) Central, Peripheral, Observer, or Broadcaster roles
- Switches between central and peripheral roles on-the-go
- Standard Bluetooth Low Energy profiles and services for interoperability
- Custom profile and service for specific use cases

Benefits

The CYBLE-022001-00 module is provided as a turnkey solution, including all necessary hardware required to use BLE communication standards.

- Proven, qualified, and certified hardware design ready to use
- Small footprint (10 × 10 mm × 1.80 mm), perfect for space constrained applications
- Reprogrammable architecture
- Fully certified module eliminates the time needed for design, development and certification processes
- Bluetooth SIG qualified with QDID and Declaration ID
- Flexible communication protocol support
- PSoC CreatorTM provides an easy-to-use integrated design environment (IDE) to configure, develop, program, and test a BLE application

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More Information

Cypress provides a wealth of data at www.cypress.com to help you to select the right module for your design, and to help you to quickly and effectively integrate the module into your design.

- Overview: EZ-BLE Module Portfolio, Module Roadmap
- EZ-BLE PRoC Product Overview
- PRoC BLE Silicon Datasheet
- Application notes: Cypress offers a number of BLE application notes covering a broad range of topics, from basic to advanced level. Recommended application notes for getting started with EZ-BLE modules are:
 - □ AN96841 Getting Started with EZ-BLE Module
 - □ AN94020 Getting Started with PRoC BLE
 - □ AN97060 PSoC® 4 BLE and PRoC™ BLE Over-The-Air (OTA) Device Firmware Upgrade (DFU) Guide
 - □ AN91162 Creating a BLE Custom Profile
 - □ AN91184 PSoC 4 BLE Designing BLE Applications
 - □ AN92584 Designing for Low Power and Estimating Battery Life for BLE Applications
 - □ AN85951 PSoC® 4 CapSense® Design Guide
 - □ AN95089 PSoC® 4/PRoC™ BLE Crystal Oscillator Selection and Tuning Techniques
 - □ AN91445 Antenna Design and RF Layout Guidelines
- Technical Reference Manual (TRM):
 - □ PRoC[®] BLE Technical Reference Manual
- Knowledge Base Articles

- □ KBA97279 Pin Mapping Differences Between the EZ-BLE™ PRoC™ Evaluation Board (CY-BLE-022001-EVAL) and the BLE Pioneer Kit (CY8CKIT-042-BLE)
- □ KBA97094 RF Regulatory Certifications for EZ-BLE™ PRoC™ Module
- □ KBA97095 EZ-BLE™ Module Placement
- □ KBA213976 FAQ for BLE and Regulatory Certifications with EZ-BLE modules
- □ KBA210802 Queries on BLE Qualification and Declaration Processes
- Development Kits:
 - □ CYBLE-022001-EVAL CYBLE-022001-00 Evaluation Board
 - □ CY8CKIT-042-BLE Bluetooth® Low Energy (BLE) Pioneer Kit
 - □ CY8CKIT-002 PSoC® MiniProg3 Program and Debug Kit
- Test and Debug Tools:
 - □ CYSmart Bluetooth[®] LE Test and Debug Tool (Windows)
 - □ CYSmart Mobile Bluetooth[®] LE Test and Debug Tool (Android/iOS Mobile App)

Two Design Environments to Get You Started Quickly

PSoC[®] Creator™ Integrated Design Environment (IDE)

PSoC Creator is an Integrated Design Environment (IDE) that enables concurrent hardware and firmware editing, compiling and debugging of PSoC 3, PSoC 4, PSoC 5LP, PSoC 4 BLE, PRoC BLE, and EZ-BLE module systems with no code size limitations. PSoC peripherals are designed using schematic capture and simple graphical user interface (GUI) with over 120 pre-verified, production-ready PSoC ComponentsTM.

PSoC Components are analog and digital "virtual chips," represented by an icon that users can drag-and-drop into a design and configure to suit a broad array of application requirements.

Bluetooth Low Energy Component

The Bluetooth Low Energy Component inside PSoC Creator provides a comprehensive GUI-based configuration window that lets you quickly design BLE applications. The Component incorporates a Bluetooth Core Specification v4.1 compliant BLE protocol stack and provides API functions to enable user applications to interface with the underlying Bluetooth Low Energy Sub-System (BLESS) hardware via the stack.

EZ-Serial™ BLE Firmware Platform

The EZ-Serial Firmware Platform provides a simple way to access the most common hardware and communication features needed in BLE applications. EZ-Serial implements an intuitive API protocol over the UART interface and exposes various status and control signals through the module's GPIOs, making it easy to add BLE functionality quickly to existing designs.

Use a simple serial terminal and evaluation kit to begin development without requiring an IDE. Refer to the EZ-Serial webpage for user manuals and instructions for getting started as well as detailed reference materials.

EZ-BLE modules are pre-flashed with the EZ-Serial Firmware Platform. If EZ-Serial is not pre-loaded on your module, you can download each EZ-BLE module's firmware images on the EZ-Serial webpage.

Technical Support

- Frequently Asked Questions (FAQs): Learn more about our BLE ecosystem.
- Forum: See if your question is already answered by fellow developers on the PSoC 4 BLE and PRoC BLE forums.
- Visit our support page and create a technical support case or contact a local sales representatives. If you are in the United States, you can talk to our technical support team by calling our toll-free number: +1-800-541-4736. Select option 2 at the prompt.



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Overview

Module Description

The CYBLE-022001-00 module is a complete module designed to be soldered to the applications main board.

Module Dimensions and Drawing

Cypress reserves the right to select components (including the appropriate BLE device) from various vendors to achieve the BLE module functionality. Such selections will still guarantee that all height restrictions of the component area are maintained. Designs should be held within the physical dimensions shown in the mechanical drawings in Figure 1. All dimensions are in millimeters (mm).

Table 1. Module Design Dimensions

Dimension Item	Specification	
Module dimensions	Length (X)	10.00 ± 0.15 mm
Wodule difficults	Width (Y)	10.00 ± 0.15 mm
Antenna location dimensions	Length (X)	7.00 ± 0.15 mm
Antenna location dimensions	Width (Y)	5.00 ± 0.15 mm
PCB thickness	Height (H)	0.50 ± 0.10 mm
Shield height	Height (H)	1.10 ± 0.10 mm
Maximum component height	Height (H)	1.30 mm typical (chip antenna)
Total module thickness (bottom of module to highest component)	Height (H)	1.80 mm typical

See Figure 1 on page 5 for the mechanical reference drawing for CYBLE-022001-00.



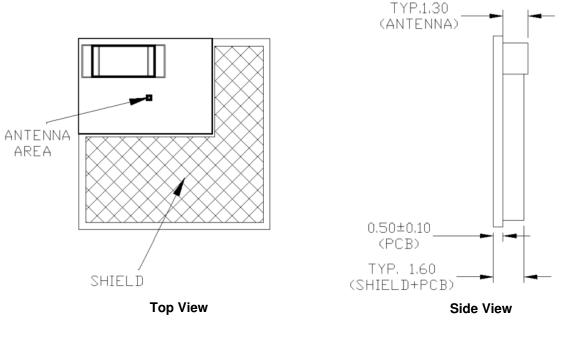
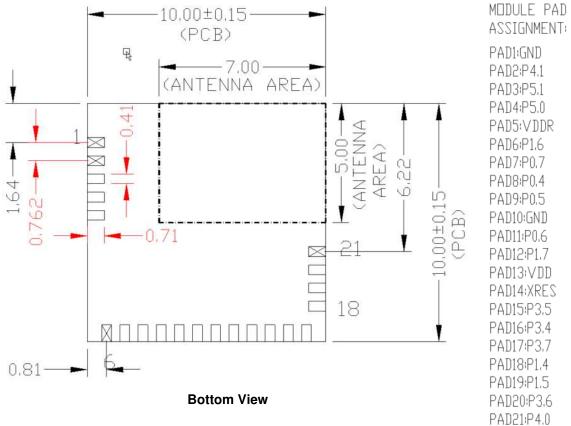


Figure 1. Module Mechanical Drawing



Note

No metal should be located beneath or above the antenna area. Only bare PCB material should be located beneath the antenna area. For more information on recommended host PCB layout, see "Recommended Host PCB Layout" on page 7.



Pad Connection Interface

As shown in the bottom view of Figure 1 on page 5, the CYBLE-022001-00 connects to the host board via solder pads on the back of the module. Table 2 and Figure 2 detail the solder pad length, width, and pitch dimensions of the CYBLE-022001-00 module.

Table 2. Solder Pad Connection Description

	Name	Connections	Connection Type	Pad Length Dimension	Pad Width Dimension	Pad Pitch
Γ	SP	21	Solder Pads	0.71 mm	0.41 mm	0.76 mm

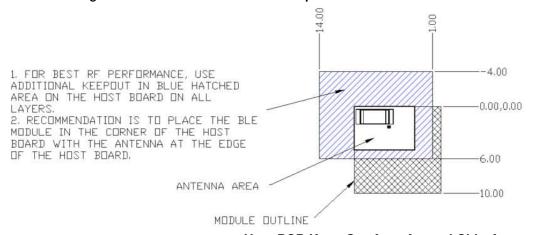
0.81

Figure 2. Solder Pad Dimensions (Seen from Bottom)

To maximize RF performance, the host layout should follow these recommendations:

- The ideal placement of the Cypress BLE module is in a corner of the host board with the chip antenna located at the far corner.
 This placement minimizes the additional recommended keep out area stated in item 2. Refer to AN96841 for module placement best practices.
- 2. To maximize RF performance, the area immediately around the Cypress BLE module chip antenna should contain an additional keep out area, where no grounding or signal traces are contained. The keep out area applies to all layers of the host board. The recommended dimensions of the host PCB keep out area are shown in Figure 3 (dimensions are in mm).

Figure 3. Recommended Host PCB Keep Out Area Around the CYBLE-022001-00 Chip Antenna



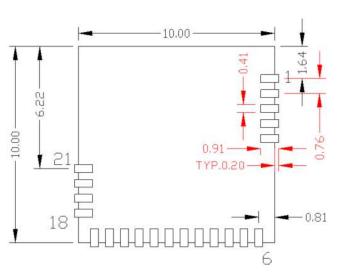
Host PCB Keep Out Area Around Chip Antenna



Recommended Host PCB Layout

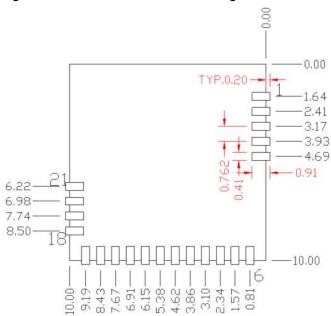
Figure 4, Figure 5, Figure 6, and Table 3 provide details that can be used for the recommended host PCB layout pattern for the CYBLE-022001-00. Dimensions are in millimeters unless otherwise noted. Pad length of 0.91 mm (0.455 mm from center of the pad on either side) shown in Figure 6 is the minimum recommended host pad length. The host PCB layout pattern can be completed using either Figure 4, Figure 5, or Figure 6. It is not necessary to use all figures to complete the host PCB layout pattern.

Figure 4. Host Layout Pattern for CYBLE-022001-00



Top View (Seen on Host PCB)

Figure 5. Module Pad Location from Origin



Top View (Seen on Host PCB)

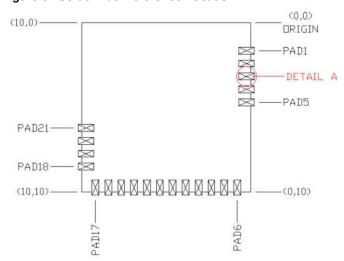


Table 3 provides the center location for each solder pad on the CYBLE-022001-00. All dimensions are referenced to the center of the solder pad. Refer to Figure 6 for the location of each module solder pad.

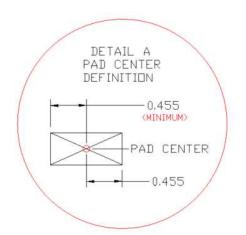
Table 3. Module Solder Pad Location

Solder Pad (Center of Pad)	Location (X,Y) from Orign (mm)	Dimension from Orign (mils)
1	(0.26, 1.64)	(10.24, 64.57)
2	(0.26, 2.41)	(10.24, 94.88)
3	(0.26, 3.17)	(10.24, 124.80)
4	(0.26, 3.93)	(10.24, 154.72)
5	(0.26, 4.69)	(10.24, 184.65)
6	(0.81, 9.74)	(31.89, 383.46)
7	(1.57, 9.74)	(61.81, 383.46)
8	(2.34, 9.74)	(92.13, 383.46)
9	(3.10, 9.74)	(122.05, 383.46)
10	(3.86, 9.74)	(151.97, 383.46)
11	(4.62, 9.74)	(181.89, 383.46)
12	(5.38, 9.74)	(211.81, 383.46)
13	(6.15, 9.74)	(242.13, 383.46)
14	(6.91, 9.74)	(272.05, 383.46)
15	(7.67, 9.74)	(301.97, 383.46)
16	(8.43, 9.74)	(331.89, 383.46)
17	(9.19, 9.74)	(361.81, 383.46)
18	(9.75, 8.50)	(383.86, 334.65)
19	(9.75, 7.74)	(383.86, 304.72)
20	(9.75, 6.98)	(383.86, 274.80)
21	(9.75, 6.22)	(383.86, 244.88)

Figure 6. Solder Pad Reference Location



Top View (Seen on Host PCB)





Digital and Analog Capabilities and Connections

Table 4 details the solder pad connection definitions and available functions for each connection pad. Table 4 lists the solder pads on CYBLE-022001-00, the BLE device port-pin, and denotes whether the function shown is available for each solder pad. Each connection is configurable for a single option shown with a .

Table 4. Solder Pad Connection Definitions

Solder Pad Number	Device Port Pin	UART	SPI	I ² C	TCPWM ^[2,3]	CapSense	WCO Out	ECO Out	LCD	SWD	GPIO
1	GND ^[4]			Gro	und Connection						
2	P4.1 ^[5]	✓(SCB1_CTS)	✓(SCB1_MISO)		✓(TCPWM0_N)	(Sensor/ C _{TANK})			/		/
3	P5.1	✓(SCB1_TX)	✓(SCB1_SCLK)	✓(SCB1_SCL)	√(TCPWM3_N)	√ (Sensor)		/	✓		✓
4	P5.0	✓(SCB1_RX)	✓(SCB1_SS0)	✓(SCB1_SDA)	✓(TCPWM3_P)	√ (Sensor)			/		✓
5	V_{DDR}			Radio Powe	r Supply (1.9V to 5	5.5V)					
6	P1.6	✓(SCB0_RTS)	✓(SCB0_SS0)		✓(TCPWM)	√ (Sensor)			/		✓
7	P0.7	✓(SCB0_CTS)	✓(SCB0_SCLK)		✓(TCPWM)	✓ (Sensor)			/	(SWDCLK)	/
8	P0.4	✓(SCB0_RX)	✓(SCB0_MOSI)	✓(SCB0_SDA)	✓(TCPWM)	√(Sensor)		/	/		/
9	P0.5	✓(SCB0_TX)	✓(SCB0_MISO)	✓(SCB0_SCL)	✓(TCPWM)	√ (Sensor)			/		✓
10	GND			Grou	und Connection						
11	P0.6	✓(SCB0_RTS)	✓(SCB0_SS0)		✓(TCPWM)	✓(Sensor)			✓	(SWDIO)	✓
12	P1.7	✓(SCB0_CTS)	✓(SCB0_SCLK)		✓(TCPWM)	√(Sensor)			/		/
13	V_{DD}			Digital Power S	Supply Input (1.71	to 5.5V)	U U				
14	XRES			External Reset I	Hardware Connect	ion Input					
15	P3.5	✓(SCB1_TX)		✓(SCB1_SCL)	✓(TCPWM)	√(Sensor)			/		✓
16	P3.4	✓(SCB1_RX)		✓(SCB1_SDA)	✓(TCPWM)	√(Sensor)			✓		✓
17	P3.7	✓(SCB1_CTS)			✓(TCPWM)	√(Sensor)	✓		/		/
18	P1.4	✓(SCB0_RX)	√(SCB0_MOSI)	✓(SCB0_SDA)	✓(TCPWM)	√(Sensor)			✓		✓
19	P1.5	✓(SCB0_TX)	✓(SCB0_MISO)	✓(SCB0_SCL)	✓(TCPWM)	√(Sensor)			/		✓
20	P3.6	✓(SCB1_RTS)			✓(TCPWM)	√(Sensor)			/		/
21	P4.0 ^[6]	✓(SCB1_RTS)	✓(SCB1_MOSI)		✓(TCPWM0_P)	√ (C _{MOD})			/		✓

Notes

- TCPWM stands for timer, counter, and PWM. If supported, the pad can be configured to any of these peripheral functions.
 TCPWM connections on ports 0, 1, 2, and 3 can be routed through the Digital Signal Interconnect (DSI) to any of the TCPWM blocks and can be either positive or negative polarity. TCPWM connections on ports 4 and 5 are direct and can only be used with the specified TCPWM block and polarity specified above.
 The main board needs to connect both GND connections (Pad 1 and Pad 10) on the module to the common ground of the system.
- When using the capacitive sensing functionality, Pad 2 (P4.1) can be connected to a C_{TANK} capacitor (located off of Cypress BLE Module). C_{Tank} should be used if implementing a shield layer on the capacitive sensor. If used, this capacitor should be placed as close to the module as possible.
- When using the capacitive sensing functionality, Pad 21 (P4.0) must be connected to a C_{MOD} capacitor (located off of Cypress BLE Module). The value of this capacitor is 2.2 nF and should be placed as close to the module as possible.

 7. If the I²S feature is used in the design, the I²S pins shall be dynamically routed to the appropriate available GPIO by PSoC Creator



Power Supply Connections and Recommended External Components

Power Connections

The CYBLE-022001-00 contains two power supply connections, VDD and VDDR. The VDD connection supplies power for both digital and analog device operation. The VDDR connection supplies power for the device radio.

VDD accepts a supply range of 1.71 V to 5.5 V. VDDR accepts a supply range of 1.9 V to 5.5 V. These specifications can be found in Table 9. The maximum power supply ripple for both power connections on the module is 100 mV, as shown in

The power supply ramp rate of VDD must be equal to or greater than that of VDDR.

Connection Options

Two connection options are available for any application:

- 1. Single supply: Connect VDD and VDDR to the same supply.
- 2. Independent supply: Power VDD and VDDR separately.

External Component Recommendation

In either connection scenario, it is recommended to place an external ferrite bead between the supply and the module connection. The ferrite bead should be positioned as close as possible to the module pin connection.

Figure 7 details the recommended host schematic options for a single supply scenario. The use of one or two ferrite beads will depend on the specific application and configuration of the CYBLE-022001-00.

Figure 8 details the recommended host schematic for an independent supply scenario.

The recommended ferrite bead value is 330 Ω , 100 MHz. (Murata BLM21PG331SN1D).

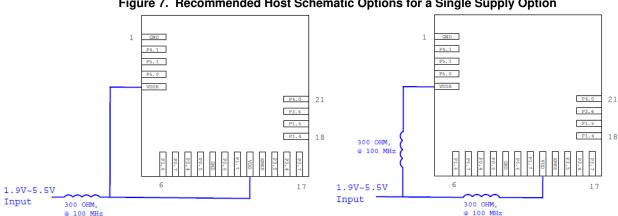


Figure 7. Recommended Host Schematic Options for a Single Supply Option

Single Ferrite Bead Option (Seen from Bottom)

Two Ferrite Bead Option (Seen from Bottom)

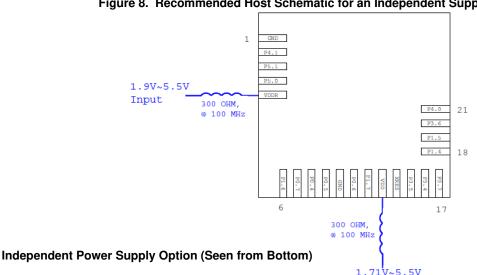


Figure 8. Recommended Host Schematic for an Independent Supply Option



The CYBLE-022001-00 schematic is shown in Figure 9.

Figure 9. CYBLE-022001-00 Schematic Diagram O P0.4 ANTENNA E1 V VDDR P0.6 P0.7 0.2pF,0201 1.5pF,0201 L1 1.8nH,0201 L2 4.7nH,0201 P1.5 P1.6 P0.6 G1
P0.2 G2
VDDD2
P0.2 G3 ×
VSSD5
VSSR5
VSSR5
G6
VSSR4
GANT
VSSR3 P0.6 VREF A1 A2 × A3 A4 A5 A6 A7 A8 VREF VSSA1 P3.3 P3.7 VSSD1 VSSA2 VCCD VDDD1 O VDD P3.7 P3.5 X B1 P2.3 VSSA3 X B3 P2.7 B4 P3.4 P3.4 P3.4 P3.6 P3.6 P3.6 P3.6 B7 XTAL320-P6.1 B8 XTAL320-P6.0 VSSD4
P0.7
P0.3
P1.0
P5.3
P1.0
VSSR2
VSSR1
VDDR1
P1.1
F6.7
F7
F8 O P4.0 P4.1 CVDDR P5.0 CYBL10X6X WLCSP-68 XRES ** * * 32.768KHz -OVDDR VDD C14 0.1uF,0201 VREF 0 C7 1.0uF,0201 C3 0.1uF,0201 VDDR0 C13 0.1uF,0201 C4 1.0uF,0201 C6 0.1uF,0201 VDD O-VCCD O C10 1.0uF,0201 C12 0.1uF,0201 C5 1.0uF,0201 P4.0 21 C9 0.1uF,0201 P3.6 C8 1.0uF,0201 18

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Critical Components List

Table 5 details the critical components used in the CYBLE-022001-00 module.

Table 5. Critical Component List

Component	Reference Designator	Description
Silicon	U1	68-pin WLCSP PRoC with BLE
Crystal	Y1	24.000 MHz, 10PF
Crystal	Y2	32.768 kHz, 12.5PF
Antenna	E1	2.4 – 2.5 GHz chip antenna

Antenna Design

Table 6 details the chip antenna used in the CYBLE-022001-00 module. The specifications listed are according to the vendor's datasheet. The Cypress module performance improves many of these characteristics. For more information, see Table 8.

Table 6. Chip Antenna Specifications

ltem	Description
Chip Antenna Manufacturer	Johanson Technology Inc.
Chip Antenna Part Number	2450AT18B100
Frequency Range	2400–2500 MHz
Peak Gain	0.5-dBi typical
Average Gain	-0.5-dBi typical
Return Loss	9.5-dB minimum



Electrical Specification

Table 7 details the absolute maximum electrical characteristics for the Cypress BLE module.

Table 7. CYBLE-022001-00 Absolute Maximum Ratings

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
V _{DDD_ABS}	Analog, digital, or radio supply relative to V_{SS} ($V_{SSD} = V_{SSA}$)	-0.5	_	6	٧	Absolute maximum
V _{CCD_ABS}	Direct digital core voltage input relative to V _{SSD}	-0.5	_	1.95	٧	Absolute maximum
V _{DDD_RIPPLE}	Maximum power supply ripple for V_{DD} and V_{DDR} input voltage	-	-	100	mV	3.0V supply Ripple frequency of 100 kHz to 750 kHz
V _{GPIO_ABS}	GPIO voltage	-0.5	_	VDD +0.5	V	Absolute maximum
I _{GPIO_ABS}	Maximum current per GPIO	-25	_	25	mA	Absolute maximum
I _{GPIO_injection}	GPIO injection current: Maximum for $V_{IH} > V_{DD}$ and minimum for $V_{IL} < V_{SS}$	-0.5	-	0.5	mA	Absolute maximum current injected per pin
LU	Pin current for latch up	-200		200	mA	_

Table 8 details the RF characteristics for the Cypress BLE module.

Table 8. CYBLE-022001-00 RF Performance Characteristics

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
RF _O	RF output power on ANT	-18	0	3		Configurable via register settings
RX _S	RF receive sensitivity on ANT	-	-87	-		Guaranteed by design simulation
F _R	Module frequency range	2400	_	2480	MHz	-
G _P	Peak gain	_	0.5	-	dBi	_
G _{Avg}	Average gain	_	-0.5	-	dBi	_
RL	Return loss	_	-10.5	_	dB	-

Table 9 through Table 48 list the module level electrical characteristics for the CYBLE-022001-00. All specifications are valid for -40 °C \leq TA \leq 85 °C and TJ \leq 100 °C, except where noted. Specifications are valid for 1.71 V to 5.5 V, except where noted.

Table 9. CYBLE-022001-00 DC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
V_{DD1}	Power supply input voltage	1.8	_	5.5	V	With regulator enabled
V _{DD2}	Power supply input voltage unregulated	1.71	1.8	1.89	٧	Internally unregulated supply
V _{DDR1}	Radio supply voltage (radio on)	1.9	_	5.5	V	-
V _{DDR2}	Radio supply voltage (radio off)	1.71	_	5.5	V	-
Active Mode,	V _{DD} = 1.71 V to 5.5 V					
I _{DD3}	Execute from flash; CPU at 3 MHz	_	1.7	_	mA	T = 25 °C, V _{DD} = 3.3 V
I _{DD4}	Execute from flash; CPU at 3 MHz	_	_	_	mA	T = -40 °C to 85 °C
I _{DD5}	Execute from flash; CPU at 6 MHz	-	2.5	_	mA	T = 25 °C, V _{DD} = 3.3 V
I _{DD6}	Execute from flash; CPU at 6 MHz	_	_	_	mA	T = -40 °C to 85 °C
I _{DD7}	Execute from flash; CPU at 12 MHz	_	4	_	mA	T = 25 °C, V _{DD} = 3.3 V



Table 9. CYBLE-022001-00 DC Specifications (continued)

Execute from flash; CPU at 24 MHz	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
Execute from flash; CPU at 24 MHz	I _{DD8}	Execute from flash; CPU at 12 MHz	_	_	_	mA	T = -40 °C to 85 °C
Execute from flash; CPU at 48 MHz	I _{DD9}	Execute from flash; CPU at 24 MHz	-	7.1	-	mA	
Execute from flash; CPU at 48 MHz	I _{DD10}	Execute from flash; CPU at 24 MHz	_	_	_	mA	T = -40 °C to 85 °C
Siep Mode, V_DD = 1.8 V to 5.5 V	I _{DD11}	Execute from flash; CPU at 48 MHz	_	13.4	_	mA	
Mode	I _{DD12}	Execute from flash; CPU at 48 MHz	_	_	_	mA	T = -40 °C to 85 °C
Side Mode, V_DD and V_DDR = 1.9 V to 5.5 V	Sleep Mode, \	V _{DD} = 1.8 V to 5.5 V				•	
ECO on	I _{DD13}	IMO on	_	_	_	mA	T = 25 °C, V _{DD} = 3.3 V, SYSCLK = 3 MHz
Deep-Sleep Mode, V _{DD} = 1.8 V to 3.6 V	Sleep Mode, \	V _{DD} and V _{DDR} = 1.9 V to 5.5 V				•	
DD15	I _{DD14}	ECO on	_	_	_	mA	$T = 25$ °C, $V_{DD} = 3.3$ V, SYSCLK = 3 MHz
DD15	Deep-Sleep M	lode, V _{DD} = 1.8 V to 3.6 V					
WDT with WCO on	I _{DD15}	WDT with WCO on	_	1.5	-	μΑ	T = 25 °C, V _{DD} = 3.3 V
DD17	I _{DD16}	WDT with WCO on	_	_	_	μΑ	
Deep-Sleep Mode, V _{DD} = 1.71 V to 1.89 V (Regulator Bypassed)	I _{DD17}	WDT with WCO on	_	_	_	μΑ	
DD19 WDT with WCO on - -	I _{DD18}	WDT with WCO on	_	_	_	μΑ	T = -40 °C to 85 °C
WDT with WCO on μA T = -40 °C to 85 °C	Deep-Sleep M		ssed)				
Itibernate Mode, V_DD = 1.8 V to 3.6 V	I _{DD19}		_	_	_	μΑ	
GPIO and reset active	I _{DD20}		_	_	_	μΑ	T = -40 °C to 85 °C
Stop-mode current (V _{DD})	Hibernate Mo	de, V _{DD} = 1.8 V to 3.6 V				_	T
Stop-mode current (V _{DD}) Stop-mode current (V _{DD}) Company Stop-mode current (V _{DD}) Company	I _{DD27}		_	150	_	nA	$V_{DD} = 3.3 \text{ V}$
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	I _{DD28}		_	_	_	nA	T = -40 °C to 85 °C
DD29 GPIO and reset active	Hibernate Mo	de, V _{DD} = 3.6 V to 5.5 V					,
Stop Mode, $V_{DD} = 1.8 \text{ V to } 3.6 \text{ V}$ DD33 Stop-mode current (V_{DD}) - 20 - nA T = 25 °C, V_{DD} = 3.3 V DD34 Stop-mode current (V_{DDR}) - 40 nA T = 25 °C, V_{DDR} = 3.3 V DD35 Stop-mode current (V_{DD}) - - - nA T = -40 °C to 85 °C DD36 Stop-mode current (V_{DDR}) - - - nA T = -40 °C to 85 °C, V_{DDR} = 1.9 V to 3.6 V Stop Mode, $V_{DD} = 3.6 \text{ V to } 5.5 \text{ V}$ - - - nA T = 25 °C, V_{DDR} = 5 V DD37 Stop-mode current (V_{DD}) - - - nA T = 25 °C, V_{DDR} = 5 V DD38 Stop-mode current (V_{DDR}) - - - nA T = 25 °C, V_{DDR} = 5 V DD39 Stop-mode current (V_{DD}) - - - nA T = -40 °C to 85 °C	I _{DD29}	GPIO and reset active	_	_	_	nA	$V_{DD} = 5 \text{ V}$
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	I _{DD30}		_	_	_	nA	T = -40 °C to 85 °C
Stop-mode current (V _{DD})	Stop Mode, V	_{DD} = 1.8 V to 3.6 V					,
Stop-mode current (V _{DDR}) - 40 - MA V _{DDR} = 3.3 V V _{DDR} = 3.3 V V _{DDS} Stop-mode current (V _{DDR}) - - nA T = -40 °C to 85 °C V _{DDR} = 1.9 V to 3.6 V Stop-mode current (V _{DDR}) - - nA T = 25 °C V _{DDR} = 5 V V _{DDR} =	I _{DD33}	Stop-mode current (V _{DD})	_	20	_	nA	$V_{DD} = 3.3 \text{ V}$
Stop-mode current (V _{DDR}) Stop-mode current (V _{DDR}) $\frac{1}{2}$ NA $\frac{1}{2}$	I _{DD34}	Stop-mode current (V _{DDR})	_	40		nA	T = 25 °C, V _{DDR} = 3.3 V
DD36 Stop-mode current (V _{DDR}) - - - - InA V _{DDR} = 1.9 V to 3.6 V Stop Mode, V _{DD} = 3.6 V to 5.5 V DD37 Stop-mode current (V _{DD}) - - - nA T = 25 °C, V _{DD} = 5 V DD38 Stop-mode current (V _{DDR}) - - - nA T = 25 °C, V _{DDR} = 5 V DD39 Stop-mode current (V _{DD}) - - nA T = -40 °C to 85 °C	I _{DD35}	Stop-mode current (V _{DD})	_	_	_	nA	
Stop-mode current (V_{DD}) Stop-mode current (V_{DD}) T = 25 °C, V_{DD} = 5 V Stop-mode current (V_{DDR}) Stop-mode current (V_{DDR}) Stop-mode current (V_{DD}) T = 25 °C, V_{DDR} = 5 V T = 25 °C, V_{DDR} = 5 V T = 25 °C, V_{DDR} = 5 V	I _{DD36}	Stop-mode current (V _{DDR})	_	_	_	nA	
Stop-mode current (V_{DD}) Stop-mode current (V_{DD}) Stop-mode current (V_{DDR}) Stop-mode current (V_{DDR}) Stop-mode current (V_{DDR}) Stop-mode current (V_{DD}) NA T = 25 °C, $V_{DDR} = 5 V$ T = 25 °C, $V_{DDR} = 5 V$ NA T = -40 °C to 85 °C	Stop Mode, V	_{DD} = 3.6 V to 5.5 V					
Stop-mode current (V_{DDR}) Stop-mode current (V_{DDR}) Stop-mode current (V_{DD}) nA $V_{DDR} = 5 V$ The stop-mode current (V_{DD}) The stop-mode current (V_{DD}) The stop-mode current (V_{DD}) The stop-mode current (V_{DDR})	I _{DD37}	Stop-mode current (V _{DD})	_	_		nA	
0, 1, 1, 10, 10, 10, 10, 10, 10, 10, 10,	I _{DD38}	Stop-mode current (V _{DDR})	_	_	_	nA	
Stop-mode current (V_{DDR})	I _{DD39}	Stop-mode current (V _{DD})	_	_	_	nA	T = -40 °C to 85 °C
	I _{DD40}	Stop-mode current (V _{DDR})	_	_	-	nA	T = -40 °C to 85 °C



Table 10. AC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
F _{CPU}	CPU frequency	DC	_	48	MHz	1.71 V ≤ V _{DD} ≤ 5.5 V
T _{SLEEP}	Wakeup from Sleep mode	_	0	_	μs	Guaranteed by characterization
T _{DEEPSLEEP}	Wakeup from Deep-Sleep mode	_	_	25	μs	24-MHz IMO. Guaranteed by characterization
T _{HIBERNATE}	Wakeup from Hibernate mode	_	_	2	ms	Guaranteed by characterization
T _{STOP}	Wakeup from Stop mode	_	_	2	ms	XRES wakeup

GPIO

Table 11. GPIO DC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
	Input voltage HIGH threshold	$0.7 \times V_{DD}$	_	_	V	CMOS input
V _{IH} ^[8]	LVTTL input, V _{DD} < 2.7 V	$0.7 \times V_{DD}$	-	_	V	-
	LVTTL input, $V_{DD} \ge 2.7 \text{ V}$	2.0	-	_	V	-
	Input voltage LOW threshold	_	-	$0.3 \times V_{DD}$	V	CMOS input
V _{IL}	LVTTL input, V _{DD} < 2.7 V	_	-	0.3× V _{DD}	V	-
	LVTTL input, $V_{DD} \ge 2.7 \text{ V}$	_	_	0.8	V	-
V.	Output voltage HIGH level	V _{DD} -0.6	_	_	V	$I_{OH} = 4 \text{ mA at } 3.3\text{-V V}_{DD}$
V _{OH}	Output voltage HIGH level	V _{DD} -0.5	-	_	V	I_{OH} = 1 mA at 1.8-V V_{DD}
	Output voltage LOW level	_	_	0.6	V	I_{OL} = 8 mA at 3.3-V V_{DD}
V _{OL}	Output voltage LOW level	_	_	0.6	V	I _{OL} = 4 mA at 1.8-V V _{DD}
	Output voltage LOW level	_	_	0.4	V	I_{OL} = 3 mA at 3.3-V V_{DD}
R _{PULLUP}	Pull-up resistor	3.5	5.6	8.5	kΩ	-
R _{PULLDOWN}	Pull-down resistor	3.5	5.6	8.5	kΩ	-
I _{IL}	Input leakage current (absolute value)	_	_	2	nA	25 °C, V _{DD} = 3.3 V
I _{IL_CTBM}	Input leakage on CTBm input pins	_	_	4	nA	-
C _{IN}	Input capacitance	_	_	7	pF	-
V _{HYSTTL}	Input hysteresis LVTTL	25	40	_	mV	V _{DD} > 2.7 V
V _{HYSCMOS}	Input hysteresis CMOS	$0.05 \times V_{DD}$	_	_	1	-
I _{DIODE}	Current through protection diode to V_{DD}/V_{SS}	_	_	100	μΑ	-
I _{TOT_GPIO}	Maximum total source or sink chip current	_	_	200	mA	-

Note 8. V_{IH} must not exceed V_{DD} + 0.2 V.



Table 12. GPIO AC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
T _{RISEF}	Rise time in Fast-Strong mode	2	_	12	ns	3.3-V V_{DDD} , $C_{LOAD} = 25 \text{ pF}$
T _{FALLF}	Fall time in Fast-Strong mode	2	-	12	ns	$3.3\text{-V V}_{DDD}, C_{LOAD} = 25 \text{ pF}$
T _{RISES}	Rise time in Slow-Strong mode	10	-	60	ns	$3.3-V V_{DDD}, C_{LOAD} = 25 pF$
T _{FALLS}	Fall time in Slow-Strong mode	10	-	60	ns	$3.3\text{-V V}_{DDD}, C_{LOAD} = 25 \text{ pF}$
F _{GPIOUT1}	GPIO Fout; 3.3 V \leq V _{DD} \leq 5.5 V Fast-Strong mode	_	_	33	MHz	90/10%, 25 pF load, 60/40 duty cycle
F _{GPIOUT2}	GPIO Fout; 1.7 $V \le V_{DD} \le 3.3 \text{ V}$ Fast-Strong mode	_	_	16.7	MHz	90/10%, 25 pF load, 60/40 duty cycle
F _{GPIOUT3}	GPIO Fout; 3.3 V \leq V _{DD} \leq 5.5 V Slow-Strong mode	_	_	7	MHz	90/10%, 25 pF load, 60/40 duty cycle
F _{GPIOUT4}	GPIO Fout; 1.7 V \leq V _{DD} \leq 3.3 V Slow-Strong mode	_	_	3.5	MHz	90/10%, 25 pF load, 60/40 duty cycle
F _{GPIOIN}	GPIO input operating frequency 1.71 V \leq V _{DD} \leq 5.5 V	_	_	48	MHz	90/10% V _{IO}

Table 13. OVT GPIO DC Specifications (P5_0 and P5_1 Only)

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
I _{IL}	Input leakage (absolute value). $V_{IH} > V_{DD}$	-	-	10	μΑ	25°C, V _{DD} = 0 V, V _{IH} = 3.0 V
V_{OL}	Output voltage LOW level	1	_	0.4	V	$I_{OL} = 20 \text{ mA}, V_{DD} > 2.9 \text{ V}$

Table 14. OVT GPIO AC Specifications (P5_0 and P5_1 Only)

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
T _{RISE_OVFS}	Output rise time in Fast-Strong mode	1.5	1	12	ns	25-pF load, 10%-90%, V _{DD} =3.3 V
T _{FALL_OVFS}	Output fall time in Fast-Strong mode	1.5	-	12	ns	25-pF load, 10%-90%, V _{DD} =3.3 V
T _{RISESS}	Output rise time in Slow-Strong mode	10	1	60	ns	25 pF load, 10%-90%, V _{DD} = 3.3 V
T _{FALLSS}	Output fall time in Slow-Strong mode	10	1	60	ns	25 pF load, 10%-90%, V _{DD} = 3.3 V
F _{GPIOUT1}	GPIO F_{OUT} ; 3.3 $V \le V_{DD} \le 5.5 V$ Fast-Strong mode	-	1	24	MHz	90/10%, 25 pF load, 60/40 duty cycle
F _{GPIOUT2}	GPIO F_{OUT} ; 1.71 $V \le V_{DD} \le 3.3 V$ Fast-Strong mode	-	ı	16	MHz	90/10%, 25 pF load, 60/40 duty cycle

XRES

Table 15. XRES DC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
V _{IH}	Input voltage HIGH threshold	$0.7 \times V_{DDD}$	_	_	V	CMOS input
V_{IL}	Input voltage LOW threshold	_	_	$0.3 \times V_{DDD}$	V	CMOS input
R _{PULLUP}	Pull-up resistor	3.5	5.6	8.5	kΩ	-
C _{IN}	Input capacitance	_	3	_	pF	-
V _{HYSXRES}	Input voltage hysteresis	_	100	_	mV	_
I _{DIODE}	Current through protection diode to V_{DD}/V_{SS}	_	-	100	μΑ	-



Table 16. XRES AC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
T _{RESETWIDTH}	Reset pulse width	1	-	_	μs	_

Temperature Sensor

Table 17. Temperature Sensor Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
T _{SENSACC}	Temperature-sensor accuracy	- 5	±1	5	°C	−40 to +85 °C

SAR ADC

Table 18. SAR ADC DC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
A_RES	Resolution	-	_	12	bits	
A_CHNIS_S	Number of channels - single-ended	_	-	6		6 full-speed ^[9]
A-CHNKS_D	Number of channels - differential	-	_	3		Diff inputs use neighboring I/O ^[9]
A-MONO	Monotonicity	_	_	_		Yes
A_GAINERR	Gain error	-	_	±0.1	%	With external reference
A_OFFSET	Input offset voltage	-	-	2	mV	Measured with 1-V V _{REF}
A_ISAR	Current consumption	_	_	1	mA	
A_VINS	Input voltage range - single-ended	V _{SS}	_	V_{DDA}	V	
A_VIND	Input voltage range - differential	V_{SS}	_	V_{DDA}	V	
A_INRES	Input resistance	_	_	2.2	kΩ	
A_INCAP	Input capacitance	_	_	10	pF	
VREFSAR	Trimmed internal reference to SAR	-1	_	1	%	Percentage of Vbg (1.024 V)

Table 19. SAR ADC AC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
A_PSRR	Power-supply rejection ratio	70	_	_	dB	Measured at 1-V reference
A_CMRR	Common-mode rejection ratio	66	_	_	dB	
A_SAMP	Sample rate	_	_	1	Msps	806 Ksps for More Part Numbers devices
Fsarintref	SAR operating speed without external ref. bypass	-	_	100	Ksps	12-bit resolution
A_SNR	Signal-to-noise ratio (SNR)	65	_	_	dB	F _{IN} = 10 kHz
A_BW	Input bandwidth without aliasing	_	_	A_SAMP/2	kHz	
A_INL	Integral nonlinearity. V _{DD} = 1.71 V to 5.5 V, 1 Msps	-1.7	_	2	LSB	$V_{REF} = 1 \text{ V to } V_{DD}$

Note

A maximum of six single-ended ADC Channels can be accomplished only if the amux buses are not being used for other functionality (such as CapSense). If
the amux buses are being used for other functionality, then the maximum number of single-ended ADC channels is four. Similarly, if the amux buses are being
used for other functionalty, then the maximum number of differential ADC channels is two.



Table 19. SAR ADC AC Specifications (continued)

Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
A_INL	Integral nonlinearity. $V_{DDD} = 1.71 \text{ V to } 3.6 \text{ V},$ 1 Msps	-1.5	_	1.7	LSB	$V_{REF} = 1.71 \text{ V to } V_{DD}$
A_INL	Integral nonlinearity. $V_{DD} = 1.71 \text{ V to } 5.5 \text{ V},$ 500 ksps	-1.5	_	1.7	LSB	$V_{REF} = 1 \text{ V to } V_{DD}$
A_dnl	Differential nonlinearity. V _{DD} = 1.71 V to 5.5 V, 1 Msps	- 1	_	2.2	LSB	$V_{REF} = 1 \text{ V to } V_{DD}$
A_DNL	Differential nonlinearity. V _{DD} = 1.71 V to 3.6 V, 1 Msps	-1	_	2	LSB	$V_{REF} = 1.71 \text{ V to } V_{DD}$
A_DNL	Differential nonlinearity. V _{DD} = 1.71 V to 5.5 V, 500 ksps	– 1	_	2.2	LSB	$V_{REF} = 1 \text{ V to } V_{DD}$
A_THD	Total harmonic distortion	_	_	-65	dB	F _{IN} = 10 kHz

CSD

CSD Block Specifications

Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
V _{CSD}	Voltage range of operation	1.71	_	5.5	V	
IDAC1	DNL for 8-bit resolution	-1	_	1	LSB	
IDAC1	INL for 8-bit resolution	-3	_	3	LSB	
IDAC2	DNL for 7-bit resolution	-1	_	1	LSB	
IDAC2	INL for 7-bit resolution	-3	_	3	LSB	
SNR	Ratio of counts of finger to noise	5	_	_	Ratio	Capacitance range of 9 pF to 35 pF, 0.1-pF sensitivity. Radio is not operating during the scan
I _{DAC1_CRT1}	Output current of IDAC1 (8 bits) in High range	_	612	_	μА	
I _{DAC1_CRT2}	Output current of IDAC1 (8 bits) in Low range	_	306	_	μΑ	
I _{DAC2_CRT1}	Output current of IDAC2 (7 bits) in High range	_	305	_	μА	
I _{DAC2_CRT2}	Output current of IDAC2 (7 bits) in Low range	_	153	_	μА	



Digital Peripherals

Timer

Table 20. Timer DC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
I _{TIM1}	Block current consumption at 3 MHz	_	_	42	μΑ	16-bit timer
I _{TIM2}	Block current consumption at 12 MHz	-	_	130	μΑ	16-bit timer
I _{TIM3}	Block current consumption at 48 MHz	_	_	535	μΑ	16-bit timer

Table 21. Timer AC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
T _{TIMFREQ}	Operating frequency	F _{CLK}	_	48	MHz	
T _{CAPWINT}	Capture pulse width (internal)	2 × T _{CLK}	_	-	ns	
T _{CAPWEXT}	Capture pulse width (external)	2 × T _{CLK}	_	-	ns	
T _{TIMRES}	Timer resolution	T _{CLK}	_	_	ns	
T _{TENWIDINT}	Enable pulse width (internal)	2 × T _{CLK}	_	-	ns	
T _{TENWIDEXT}	Enable pulse width (external)	2 × T _{CLK}	_	-	ns	
T _{TIMRESWINT}	Reset pulse width (internal)	2 × T _{CLK}	_	-	ns	
T _{TIMRESEXT}	Reset pulse width (external)	2 × T _{CLK}	_	_	ns	

Counter

Table 22. Counter DC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
I _{CTR1}	Block current consumption at 3 MHz	_	_	42	μΑ	16-bit counter
I _{CTR2}	Block current consumption at 12 MHz	_	_	130	μΑ	16-bit counter
I _{CTR3}	Block current consumption at 48 MHz	ı	1	535	μΑ	16-bit counter

Table 23. Counter AC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
T _{CTRFREQ}	Operating frequency	F _{CLK}	_	48	MHz	
T _{CTRPWINT}	Capture pulse width (internal)	2 × T _{CLK}	_	_	ns	
T _{CTRPWEXT}	Capture pulse width (external)	2 × T _{CLK}	_	_	ns	
T _{CTRES}	Counter Resolution	T _{CLK}	_	_	ns	
T _{CENWIDINT}	Enable pulse width (internal)	2 × T _{CLK}	_	_	ns	
T _{CENWIDEXT}	Enable pulse width (external)	2 × T _{CLK}	_	_	ns	
T _{CTRRESWINT}	Reset pulse width (internal)	2 × T _{CLK}	_	_	ns	
T _{CTRRESWEXT}	Reset pulse width (external)	2 × T _{CLK}	-	-	ns	



Pulse Width Modulation (PWM)

Table 24. PWM DC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
I _{PWM1}	Block current consumption at 3 MHz	-	_	42	μΑ	16-bit PWM
I _{PWM2}	Block current consumption at 12 MHz	_	_	130	μΑ	16-bit PWM
I _{PWM3}	Block current consumption at 48 MHz	_	_	535	μΑ	16-bit PWM

Table 25. PWM AC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
T _{PWMFREQ}	Operating frequency	F _{CLK}	_	48	MHz	
T _{PWMPWINT}	Pulse width (internal)	2 × T _{CLK}	_	_	ns	
T _{PWMEXT}	Pulse width (external)	2 × T _{CLK}	_	_	ns	
T _{PWMKILLINT}	Kill pulse width (internal)	2 × T _{CLK}	_	_	ns	
T _{PWMKILLEXT}	Kill pulse width (external)	2 × T _{CLK}	_	_	ns	
T _{PWMEINT}	Enable pulse width (internal)	2 × T _{CLK}	_	_	ns	
T _{PWMENEXT}	Enable pulse width (external)	2 × T _{CLK}	_	_	ns	
T _{PWMRESWINT}	Reset pulse width (internal)	2 × T _{CLK}	_	_	ns	
T _{PWMRESWEXT}	Reset pulse width (external)	2 × T _{CLK}	-	_	ns	

LCD Direct Drive

Table 26. LCD Direct Drive DC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
I _{LCDLOW}	Operating current in low-power mode	_	17.5	_	μА	16 × 4 small segment display at 50 Hz
C _{LCDCAP}	LCD capacitance per segment/common driver	_	500	5000	pF	
LCD _{OFFSET}	Long-term segment offset	_	20	_	mV	
I _{LCDOP1}	LCD system operating current V _{BIAS} = 5 V	_	2	_	mA	32 × 4 segments. 50 Hz at 25 °C
I _{LCDOP2}	LCD system operating current V _{BIAS} = 3.3 V	_	2	_	mA	32 × 4 segments 50 Hz at 25 °C

Table 27. LCD Direct Drive AC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
F _{LCD}	LCD frame rate	10	50	150	Hz	



Serial Communication

Table 28. Fixed I²C DC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
I _{I2C1}	Block current consumption at 100 kHz	_	_	50	μΑ	
I _{I2C2}	Block current consumption at 400 kHz	_	_	155	μΑ	-
I _{12C3}	Block current consumption at 1 Mbps	_	_	390	μΑ	-
I _{I2C4}	I ² C enabled in Deep-Sleep mode	_	_	1.4	μΑ	-

Table 29. Fixed I²C AC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
F _{I2C1}	Bit rate	_	-	400	kHz	

Table 30. Fixed UART DC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
I _{UART1}	Block current consumption at 100 kbps	_	_	55	μΑ	_
I _{UART2}	Block current consumption at 1000 kbps	-	_	312	μΑ	-

Table 31. Fixed UART AC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
F _{UART}	Bit rate	_	_	1	Mbps	-

Table 32. Fixed SPI DC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
I _{SPI1}	Block current consumption at 1 Mbps	_	_	360	μΑ	_
I _{SPI2}	Block current consumption at 4 Mbps	_	_	560	μΑ	_
I _{SPI3}	Block current consumption at 8 Mbps	-	_	600	μΑ	-

Table 33. Fixed SPI AC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
F _{SPI}	SPI operating frequency (master; 6x over sampling)	ı	-	8	MHz	-

Table 34. Fixed SPI Master Mode AC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
T_{DMO}	MOSI valid after SCLK driving edge	_	_	18	ns	_
T _{DSI}	MISO valid before SCLK capturing edge Full clock, late MISO sampling used	20	_	-	ns	Full clock, late MISO sampling
T _{HMO}	Previous MOSI data hold time	0	_	ı	ns	Referred to Slave capturing edge

Table 35. Fixed SPI Slave Mode AC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
T _{DMI}	MOSI valid before SCLK capturing edge	40	-	-	ns	
T _{DSO}	MISO valid after SCLK driving edge	-	-	42 + 3 × T _{CPU}	ns	
T _{DSO_ext}	MISO Valid after SCLK driving edge in external clock mode. V _{DD} < 3.0 V	-	-	50	ns	
T _{HSO}	Previous MISO data hold time	0	-	-	ns	
T _{SSELSCK}	SSEL valid to first SCK valid edge	100	_	_	ns	



Memory

Table 36. Flash DC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
V_{PE}	Erase and program voltage	1.71	_	5.5	V	_
T _{WS48}	Number of Wait states at 32–48 MHz	2	_	_		CPU execution from flash
T _{WS32}	Number of Wait states at 16–32 MHz	1	_	_		CPU execution from flash
T _{WS16}	Number of Wait states for 0–16 MHz	0	_	_		CPU execution from flash

Table 37. Flash AC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
T _{ROWWRITE} ^[10]	Row (block) write time (erase and program)	1	_	20	ms	Row (block) = 128 bytes
HOWLINAGE	Row erase time	-	_	13	ms	_
	Row program time after erase	_	_	7	ms	_
DOLINEITHOL	Bulk erase time (128 KB)	_	_	35	ms	_
T _{DEVPROG} ^[10]	Total device program time	-	_	25	seconds	_
F _{END}	Flash endurance	100 K	_	_	cycles	_
F _{RET}	Flash retention. $T_A \le 55$ °C, 100 K P/E cycles	20	_	_	years	_
F _{RET2}	Flash retention. $T_A \le 85$ °C, 10 K P/E cycles	10	_	_	years	_

System Resources

Power-on-Reset (POR)

Table 38. POR DC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
V _{RISEIPOR}	Rising trip voltage	0.80	_	1.45	V	_
V _{FALLIPOR}	Falling trip voltage	0.75	_	1.40	V	_
V _{IPORHYST}	Hysteresis	15	_	200	mV	_

Table 39. POR AC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
LLDDOD TD	Precision power-on reset (PPOR) response time in Active and Sleep modes	_	_	1	μs	-

Table 40. Brown-Out Detect

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
$V_{FALLPPOR}$	BOD trip voltage in Active and Sleep modes	1.64	1	-	V	-
V _{FALLDPSLP}	BOD trip voltage in Deep Sleep	1.4	-	_	V	_

Table 41. Hibernate Reset

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
$V_{HBRTRIP}$	BOD trip voltage in Hibernate	1.1	-	-	V	-

Note

^{10.} It can take as much as 20 ms to write to flash. During this time, the device should not be reset, or flash operations will be interrupted and cannot be relied on to have completed. Reset sources include the XRES pin, software resets, CPU lockup states and privilege violations, improper power supply levels, and watchdogs. Make certain that these are not inadvertently activated.



Voltage Monitors (LVD)

Table 42. Voltage Monitor DC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
V _{LVI1}	LVI_A/D_SEL[3:0] = 0000b	1.71	1.75	1.79	V	-
V _{LVI2}	LVI_A/D_SEL[3:0] = 0001b	1.76	1.80	1.85	V	_
V _{LVI3}	LVI_A/D_SEL[3:0] = 0010b	1.85	1.90	1.95	V	_
V_{LVI4}	LVI_A/D_SEL[3:0] = 0011b	1.95	2.00	2.05	V	_
V_{LVI5}	LVI_A/D_SEL[3:0] = 0100b	2.05	2.10	2.15	V	_
V_{LVI6}	LVI_A/D_SEL[3:0] = 0101b	2.15	2.20	2.26	V	_
V_{LVI7}	LVI_A/D_SEL[3:0] = 0110b	2.24	2.30	2.36	V	_
V_{LVI8}	LVI_A/D_SEL[3:0] = 0111b	2.34	2.40	2.46	V	_
V_{LVI9}	LVI_A/D_SEL[3:0] = 1000b	2.44	2.50	2.56	V	_
V _{LVI10}	LVI_A/D_SEL[3:0] = 1001b	2.54	2.60	2.67	V	_
V _{LVI11}	LVI_A/D_SEL[3:0] = 1010b	2.63	2.70	2.77	V	_
V _{LVI12}	LVI_A/D_SEL[3:0] = 1011b	2.73	2.80	2.87	V	_
V _{LVI13}	LVI_A/D_SEL[3:0] = 1100b	2.83	2.90	2.97	V	_
V _{LVI14}	LVI_A/D_SEL[3:0] = 1101b	2.93	3.00	3.08	V	_
V _{LVI15}	LVI_A/D_SEL[3:0] = 1110b	3.12	3.20	3.28	V	_
V _{LVI16}	LVI_A/D_SEL[3:0] = 1111b	4.39	4.50	4.61	V	-
LVI_IDD	Block current	_	_	100	μΑ	-

Table 43. Voltage Monitor AC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
T _{MONTRIP}	Voltage monitor trip time	_	_	1	μs	-

SWD Interface

Table 44. SWD Interface Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
F_SWDCLK1	$3.3~V \leq V_{DD} \leq 5.5~V$	_	_	14	MHz	SWDCLK ≤ 1/3 CPU clock frequency
F_SWDCLK2	$1.71 \text{ V} \le \text{V}_{DD} \le 3.3 \text{ V}$	_	_	7	MHz	SWDCLK ≤ 1/3 CPU clock frequency
T_SWDI_SETUP	T = 1/f SWDCLK	0.25 × T	_	_	ns	_
T_SWDI_HOLD	T = 1/f SWDCLK	0.25 × T	_	_	ns	-
T_SWDO_VALID	T = 1/f SWDCLK	_	_	0.5 × T	ns	-
T_SWDO_HOLD	T = 1/f SWDCLK	1	_	_	ns	-



Internal Main Oscillator

Table 45. IMO DC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
I _{IMO1}	IMO operating current at 48 MHz	_	_	1000	μΑ	_
I _{IMO2}	IMO operating current at 24 MHz	_	_	325	μΑ	-
I _{IMO3}	IMO operating current at 12 MHz	_	_	225	μΑ	-
I _{IMO4}	IMO operating current at 6 MHz	_	_	180	μΑ	-
I _{IMO5}	IMO operating current at 3 MHz	_	_	150	μΑ	-

Table 46. IMO AC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
F _{IMOTOL3}	Frequency variation from 3 to 48 MHz	_	_	<u>±</u> 2	%	With API-called calibration
F _{IMOTOL3}	IMO startup time	_	12	-	μs	_

Internal Low-Speed Oscillator

Table 47. ILO DC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
I_{ILO2}	ILO operating current at 32 kHz	_	0.3	1.05	μΑ	_

Table 48. ILO AC Specifications

Parameter	Description	Min	Тур	Max	Units	Details/Conditions
T _{STARTILO1}	ILO startup time	_	-	2	ms	_
F _{ILOTRIM1}	32-kHz trimmed frequency	15	32	50	kHz	_

Table 49. Recommended ECO Trim Value

Parameter	Description	Value	Details/Conditions
IH(;()+DIM	24-MHz trim value (firmware configuration)	0x00009898	Recommended trim value that needs to be loaded to register CY_SYS_XTAL_BLERD_BB_XO_CAPTRIM_REG

BLE Subsystem

Table 50. BLE Subsystem

Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
RF Receiver Spec	ification				•	•
RXS, IDLE	RX sensitivity with idle transmitter	_	-89	_	dBm	
	RX sensitivity with idle transmitter excluding Balun loss	_	- 91	_	dBm	Guaranteed by design simulation
RXS, DIRTY	RX sensitivity with dirty transmitter	_	-87	-70	dBm	RF-PHY Specification (RCV-LE/CA/01/C)
RXS, HIGHGAIN	RX sensitivity in high-gain mode with idle transmitter	_	- 91	_	dBm	
PRXMAX	Maximum input power	-10	-1	_	dBm	RF-PHY Specification (RCV-LE/CA/06/C)
CI1	Cochannel interference, Wanted signal at –67 dBm and Interferer at FRX	_	9	21	dB	RF-PHY Specification (RCV-LE/CA/03/C)



Table 50. BLE Subsystem (continued)

Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
Cl2	Adjacent channel interference Wanted signal at –67 dBm and Interferer at FRX ±1 MHz	-	3	15	dB	RF-PHY Specification (RCV-LE/CA/03/C)
Cl3	Adjacent channel interference Wanted signal at –67 dBm and Interferer at FRX ±2 MHz	ı	-29	-	dB	RF-PHY Specification (RCV-LE/CA/03/C)
Cl4	Adjacent channel interference Wanted signal at –67 dBm and Interferer at ≥FRX ±3 MHz	ı	-39	-	dB	RF-PHY Specification (RCV-LE/CA/03/C)
CI5	Adjacent channel interference Wanted Signal at –67 dBm and Interferer at Image frequency (F _{IMAGE})	ı	-20	-	dB	RF-PHY Specification (RCV-LE/CA/03/C)
Cl3	Adjacent channel interference Wanted signal at –67 dBm and Interferer at Image frequency (F _{IMAGE} ± 1 MHz)	-	-30	_	dB	RF-PHY Specification (RCV-LE/CA/03/C)
OBB1	Out-of-band blocking, Wanted signal at –67 dBm and Interferer at F = 30–2000 MHz	-30	- 27	_	dBm	RF-PHY Specification (RCV-LE/CA/04/C)
OBB2	Out-of-band blocking, Wanted signal at –67 dBm and Interferer at F = 2003–2399 MHz	- 35	-27	_	dBm	RF-PHY Specification (RCV-LE/CA/04/C)
OBB3	Out-of-band blocking, Wanted signal at –67 dBm and Interferer at F = 2484–2997 MHz	- 35	-27	_	dBm	RF-PHY Specification (RCV-LE/CA/04/C)
OBB4	Out-of-band blocking, Wanted signal a -67 dBm and Interferer at F = 3000-12750 MHz	-30	-27	_	dBm	RF-PHY Specification (RCV-LE/CA/04/C)
IMD	Intermodulation performance Wanted signal at –64 dBm and 1-Mbps BLE, third, fourth, and fifth offset channel	- 50	_	_	dBm	RF-PHY Specification (RCV-LE/CA/05/C)
RXSE1	Receiver spurious emission 30 MHz to 1.0 GHz	-	_	– 57	dBm	100-kHz measurement bandwidth ETSI EN300 328 V1.8.1
RXSE2	Receiver spurious emission 1.0 GHz to 12.75 GHz	-	_	-47	dBm	1-MHz measurement bandwidth ETSI EN300 328 V1.8.1
RF Transmitter S	pecifications				•	
TXP, ACC	RF power accuracy	-	±1	_	dB	
TXP, RANGE	RF power control range	_	20	_	dB	
TXP, 0dBm	Output power, 0-dB Gain setting (PA7)	-	0	_	dBm	
TXP, MAX	Output power, maximum power setting (PA10)	Ι	3	_	dBm	
TXP, MIN	Output power, minimum power setting (PA1)	_	-18	_	dBm	
F2AVG	Average frequency deviation for 10101010 pattern	185	_	_	kHz	RF-PHY Specification (TRM-LE/CA/05/C)